Preferred Devices

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Glassivated PNPN devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

Features

- Glassivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Sensitive Gate Triggering
 Pb–Free Packages are Available*



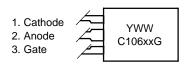
ON Semiconductor®

SCRs 4 A RMS, 200 – 600 Volts





MARKING DIAGRAM & PIN ASSIGNMENT



Y = Year

WW = Work Week

C106xx = Device Code

xx = B, D, D1, M, M1

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Characteristic			Max	Unit
Peak Repetitive Off–State Voltage (Note 1) (Sine Wave, 50–60 Hz, R_{GK} = 1 kΩ, T_C = -40° to 110°C)		V _{DRM,} V _{RRM}		V
10 = -40 10 110 0)	C106B C106D, C106D1* C106M, C106M1*		200 400 600	
On-State RMS Current (180° Conduction Angles, T _C = 80°C)		I _{T(RMS)}	4.0	А
Average On–State Current (180° Conduction Angles, T _C = 80°C)		I _{T(AV)}	2.55	А
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _J = +110°C)		I _{TSM}	20	А
Circuit Fusing Considerations (t = 8.3 ms)		l ² t	1.65	A ² s
Forward Peak Gate Power (Pulse Width ≤ 1.0 µsec, T _C = 80°C)		P_{GM}	0.5	W
Forward Average Gate Power (Pulse Width \leq 1.0 µsec, T _C = 80°C)		P _{G(AV)}	0.1	W
Forward Peak Gate Current (Pulse Width \leq 1.0 µsec, T _C = 80°C)		I _{GM}	0.2	А
Operating Junction Temperature Range		TJ	-40 to +110	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C
Mounting Torque (Note 2)		_	6.0	in. lb.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- 2. Torque rating applies with use of compression washer (B52200F006). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common.

THERMAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	°C/W
Thermal Resistance, Junction-to-Ambient		75	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8 in. from Case for 10 Seconds		260	°C

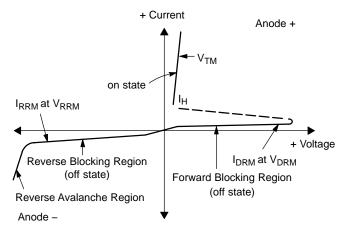
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		
Peak Repetitive Forward or Reverse Blocking Current $(V_{AK} = Rated V_{DRM} or V_{RRM}, R_{GK} = 1000 Ohms)$	T _J = 25°C T _J = 110°C	I _{DRM} , I _{RRM}	_ _	_ _	10 100	μ Α μ Α
ON CHARACTERISTICS						
Peak Forward On–State Voltage (Note 3) (I _{TM} = 4 A)		V _{TM}	_	-	2.2	V
Gate Trigger Current (Continuous dc) (Note 4) (V _{AK} = 6 Vdc, R _L = 100 Ohms)	$T_J = 25$ °C $T_J = -40$ °C	I _{GT}	_ _	15 35	200 500	μΑ
Peak Reverse Gate Voltage (I _{GR} = 10 μA)		V_{GRM}	_	_	6.0	V
Gate Trigger Voltage (Continuous dc) (Note 4) (V _{AK} = 6 Vdc, R _L = 100 Ohms)	$T_J = 25$ °C $T_J = -40$ °C	V _{GT}	0.4 0.5	0.60 0.75	0.8 1.0	V
Gate Non-Trigger Voltage (Continuous dc) (Note 4) (V _{AK} = 12 V, R _L = 100 Ohms, T _J = 110°C)		V_{GD}	0.2	-	_	V
Latching Current (V _{AK} = 12 V, I _G = 20 mA)	$T_J = 25$ °C $T_J = -40$ °C	IL	_ _	0.20 0.35	5.0 7.0	mA
Holding Current (V _D = 12 Vdc) (Initiating Current = 20 mA, Gate Open)	$T_{J} = 25^{\circ}C$ $T_{J} = -40^{\circ}C$ $T_{J} = +110^{\circ}C$	l _H	- - -	0.19 0.33 0.07	3.0 6.0 2.0	mA
DYNAMIC CHARACTERISTICS						
Critical Rate-of-Rise of Off-State Voltage (V_{AK} = Rated V_{DRM} , Exponential Waveform, R_{GK} = 10 T_J = 110°C)	00 Ohms,	dv/dt	_	8.0	-	V/µs

^{3.} Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Voltage Current Characteristic of SCR

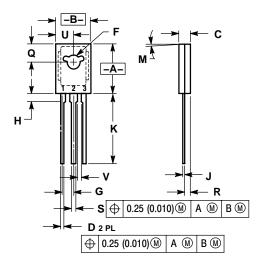
	,
Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Peak On State Voltage
I _H	Holding Current



^{4.} R_{GK} is not included in measurement.

PACKAGE DIMENSIONS

TO-225 CASE 77-09 ISSUE Z



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.425	0.435	10.80	11.04	
В	0.295	0.305	7.50	7.74	
C	0.095	0.105	2.42	2.66	
D	0.020	0.026	0.51	0.66	
F	0.115	0.130	2.93	3.30	
G	0.094 BSC		2.39 BSC		
Н	0.050	0.095	1.27	2.41	
J	0.015	0.025	0.39	0.63	
K	0.575	0.655	14.61	16.63	
M	5° TYP		5°TYP		
Q	0.148	0.158	3.76	4.01	
R	0.045	0.065	1.15	1.65	
S	0.025	0.035	0.64	0.88	
U	0.145	0.155	3.69	3.93	
٧	0.040		1.02		

STYLE 2: PIN 1. CATHODE 2. ANODE 3. GATE